Ordering number : ENN6620

P-Channel Silicon MOSFET

5LP01N

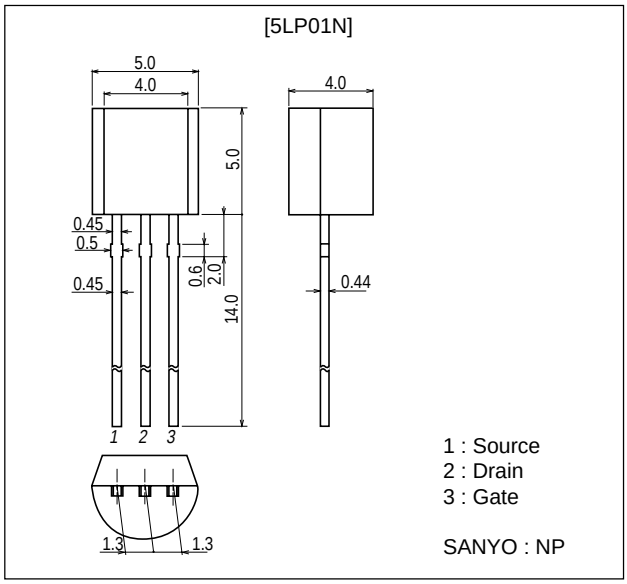
Ultrahigh-Speed Switching Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Package Dimensions

unit : mm
2178



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		-50	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		-0.07	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	-0.28	A
Allowable Power Dissipation	P_D		0.4	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=-1mA, V_{GS}=0	-50			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=-50V, V_{GS}=0			10	μA
Gate-to-Sourse Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=-10V, I_D=-100μA	-0.4		-1.4	V

Marking : XB

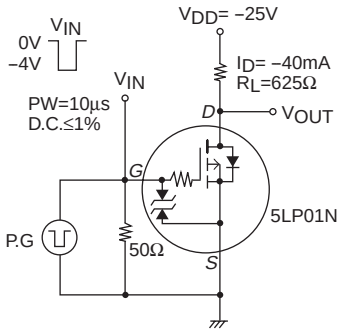
Continued on next page.

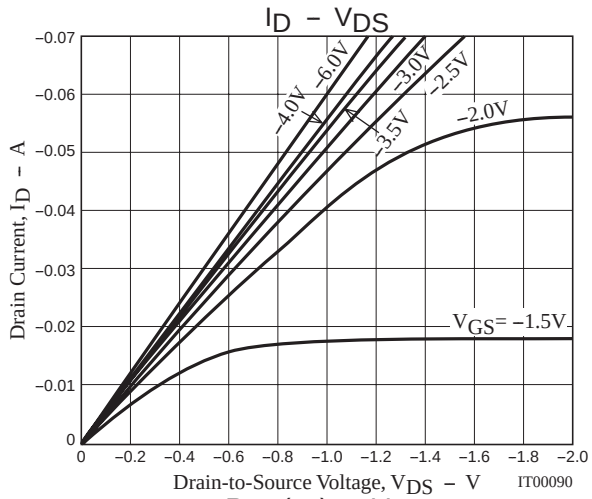
SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

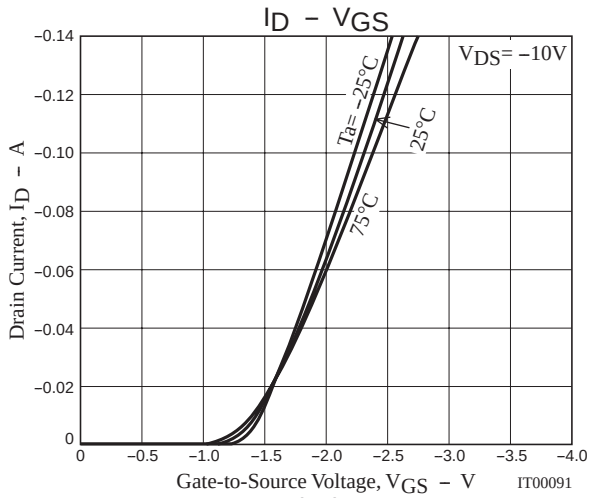
Continued from preceding page.

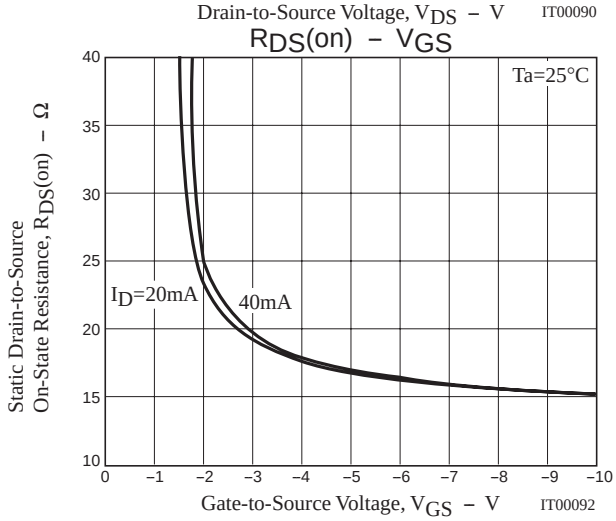
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Transfer Admittance	|yfs|	V_{DS}=–10V, I_D=–40mA	70	100		mS
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=–40mA, V_{GS}=–4V		18	23	Ω
	R_{DS}(on)2	I_D=–20mA, V_{GS}=–2.5V		20	28	Ω
	R_{DS}(on)3	I_D=–5mA, V_{GS}=–1.5V		30	60	Ω
Input Capacitance	Ciss	V_{DS}=–10V, f=1MHz		7.4		pF
Output Capacitance	Coss	V_{DS}=–10V, f=1MHz		4.2		pF
Reverse Transfer Capacitance	Crss	V_{DS}=–10V, f=1MHz		1.3		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit		20		ns
Rise Time	t_r	See specified Test Circuit		35		ns
Turn-OFF Delay Time	t_d(off)	See specified Test Circuit		160		ns
Fall Time	t_f	See specified Test Circuit		150		ns
Total Gate Charge	Qg	V_{DS}=–10V, V_{GS}=–10V, I_D=–70mA		1.40		nC
Gate-to-Source Charge	Qgs	V_{DS}=–10V, V_{GS}=–10V, I_D=–70mA		0.16		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=–10V, V_{GS}=–10V, I_D=–70mA		0.23		nC
Diode Forward Voltage	V_{SD}	I_S=–70mA, V_{GS}=0		0.85	1.2	V

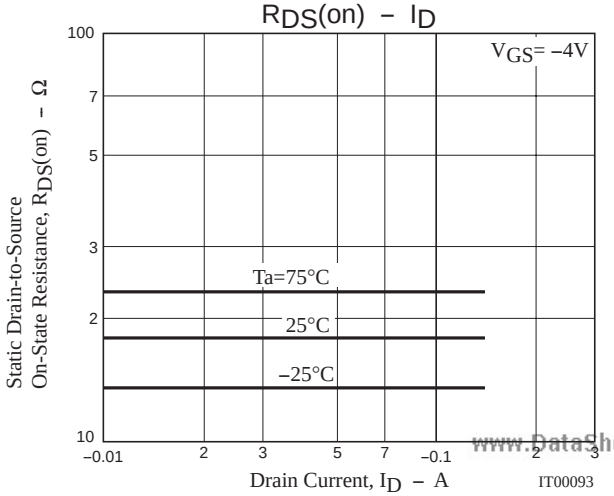
Switching Time Test Circuit

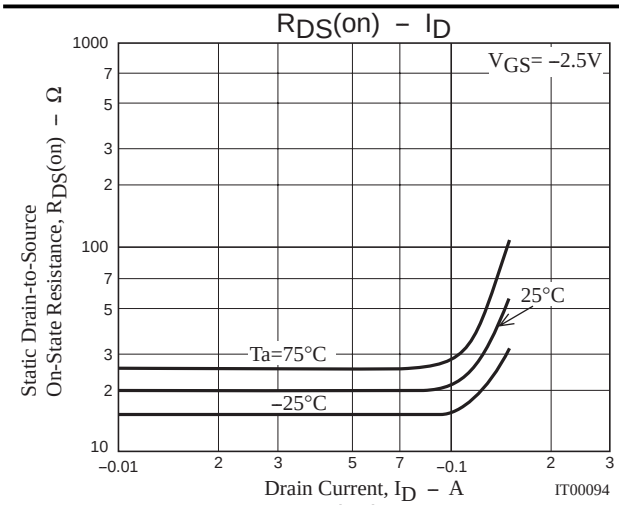


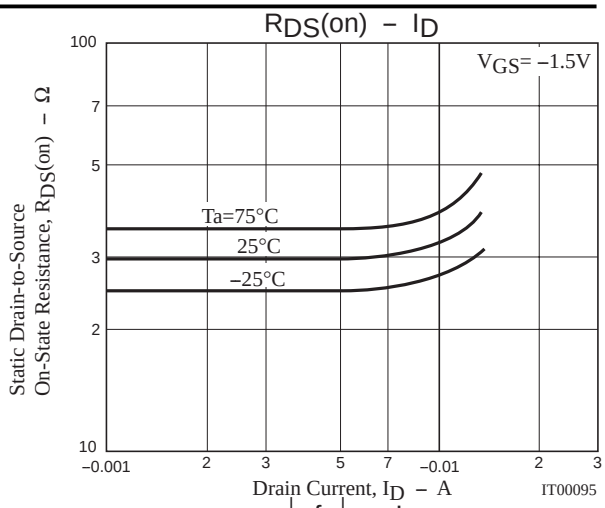


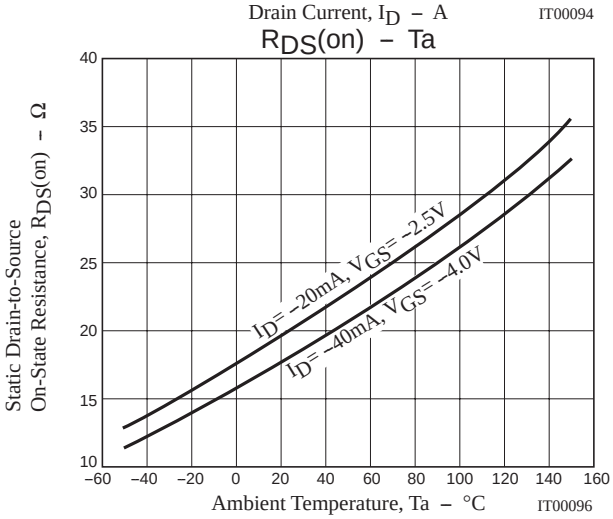


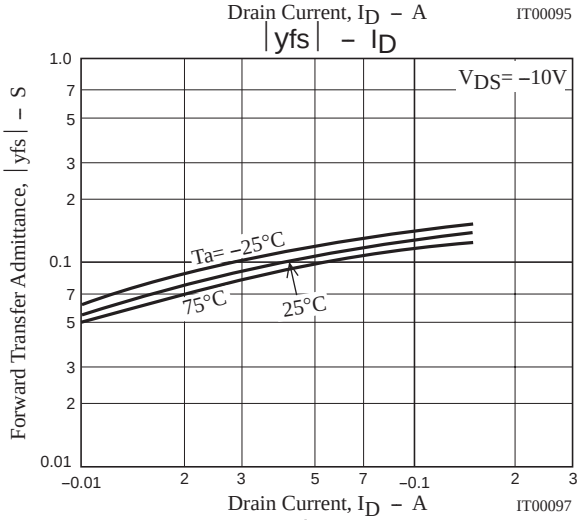


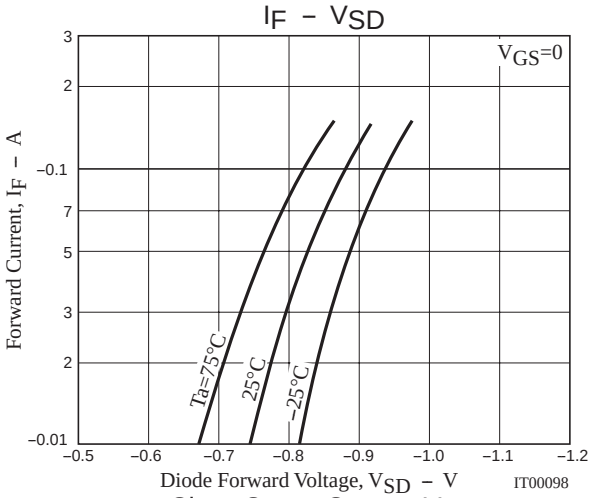


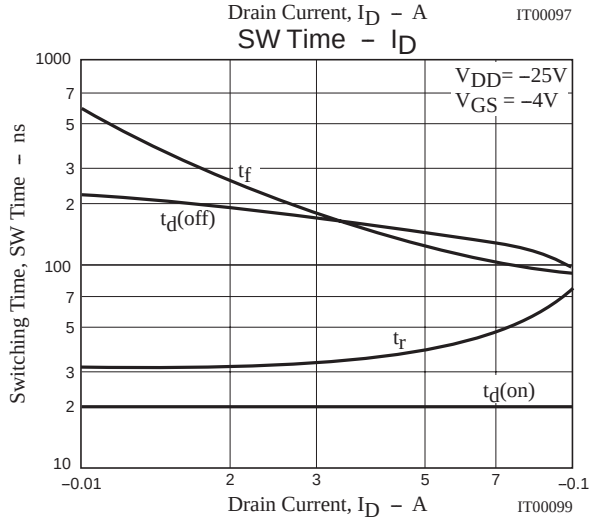


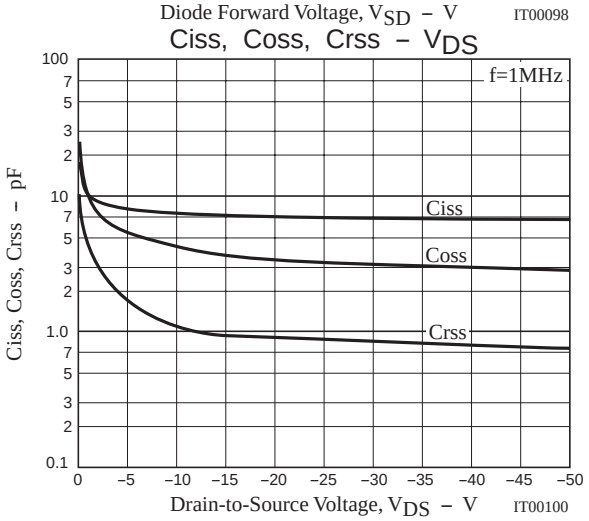


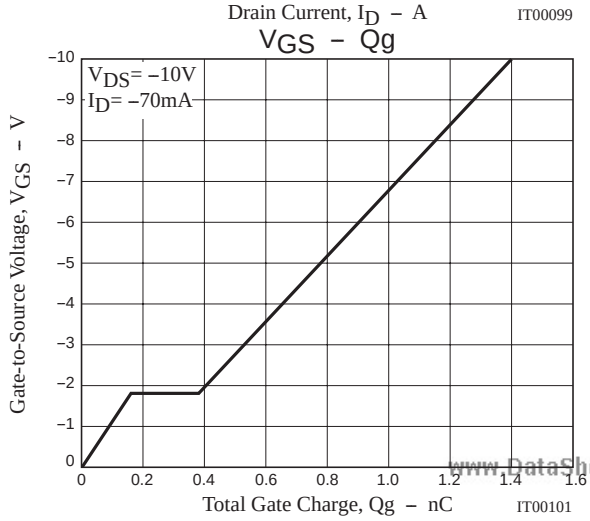


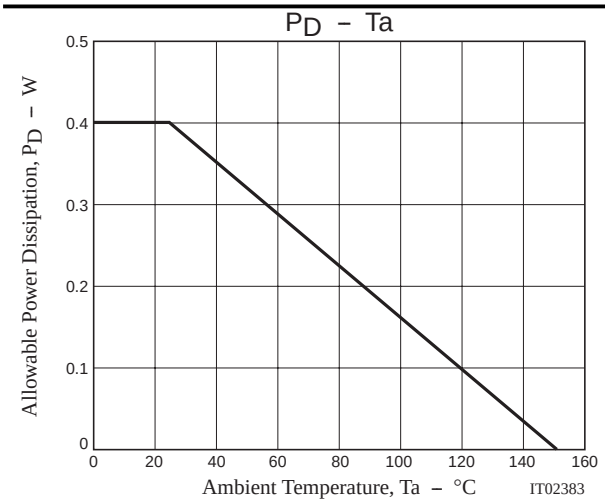












Note on usage : Since the 5LP01N is designed for high-speed switching applications, please avoid using this device in the vicinity of highly charged objects.